

**In the Claims**

This listing of claims will replace all prior versions, and listings, of claims in the application:

**Listing of Claims**

1-6. (Cancelled)

7. (Previously Presented) A high frequency substrate, comprising at least:

a first metal layer;

a first dielectric layer on the first metal layer, wherein the first dielectric layer is made of a high dielectric coefficient material;

a second metal layer on the first dielectric layer;

a second dielectric layer on the second metal layer, wherein the second dielectric layer comprises a first opening;

a third dielectric layer within the first opening and on the second metal layer, wherein the third dielectric layer is made of a low dielectric coefficient material, and a dielectric coefficient of the third dielectric layer is smaller than a dielectric coefficient of the second dielectric layer; and

a high-frequency signal transmission line on the third dielectric layer.

8. (Withdrawn) The high frequency substrate according to claim 7, wherein the second dielectric layer further comprises a second opening.

9. (Withdrawn) The high frequency substrate according to claim 8, wherein the high-frequency substrate further comprises:

a fourth dielectric layer within the second opening and on the second metal layer, wherein the fourth dielectric layer is made of a high dielectric coefficient material; and

a low-frequency signal transmission line on the fourth dielectric layer.

10. (Original) The high frequency substrate according to claim 7, wherein the second dielectric layer is made of a high dielectric coefficient material.

11. (Original) The high frequency substrate according to claim 10, wherein the high-frequency substrate further comprises a low-frequency signal transmission line on the second dielectric layer.

12. (Original) The high frequency substrate according to claim 7, wherein the value of the dielectric coefficient for the high dielectric coefficient material is more than 4.

13. (Original) The high frequency substrate according to claim 7, wherein the low dielectric coefficient material is polytetrafluoroethylene (PTFE)

14. (Original) The high frequency substrate according to claim 7, wherein the value of the dielectric coefficient for the low dielectric coefficient material is less than 4

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15. (Previously Presented) The high frequency substrate according to claim 7, wherein a top surface area of the third dielectric layer is equal to or larger than a bottom surface area of the high-frequency signal transmission line.

16-20. (Cancelled)

21-28. (Cancelled)

29. (Previously Presented) The high frequency substrate according to claim 7, wherein the first metal layer is a ground plane and the second metal layer is a power plane.

30. (Previously Presented) The high frequency substrate according to claim 7, wherein the first metal layer is a power plane and the second metal layer is a ground plane.

31-36. (Cancelled)